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BUK9535-55A



N-channel TrenchMOS logic level FET Rev. 02 — 28 April 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

Low conduction losses due to low on-state resistance

1.3 Applications

Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	55	V
I _D	drain current	T _{mb} = 25 °C	-	-	34	Α
P _{tot}	total power dissipation		-	-	85	W
Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	24	32	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	26	35	mΩ
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 14 \text{ A; } V_{sup} \leq 25 \text{ V;} \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	49	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78A (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9535-55A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-10	10	V
I_D	drain current	T _{mb} = 100 °C	-	24	Α
		T _{mb} = 25 °C	-	34	Α
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed	-	133	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	85	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
V_{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \mu s$	-15	15	V
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	34	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	133	Α
Avalanche ru	iggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 14 A; $V_{sup} \le$ 25 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	49	mJ

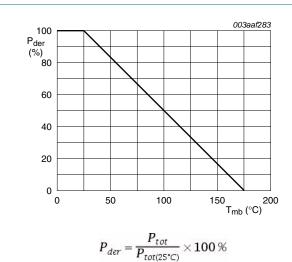


Fig 1. Normalized total power dissipation as a function of mounting base temperature

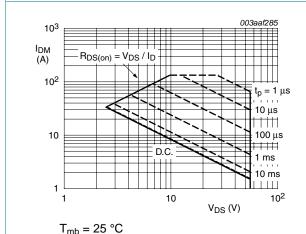
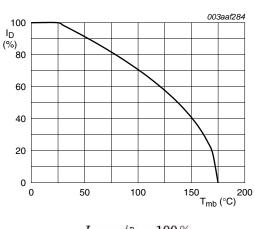


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



 $I_{der = \frac{I_D}{I_{D(25^{\circ}C)}} \times} 100 \%$

 $V_{GS} \ge 5 \text{ V}$

Fig 2. Normalized continuous drain current as a function of mounting base temperature

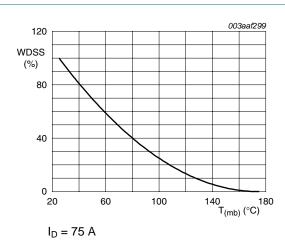
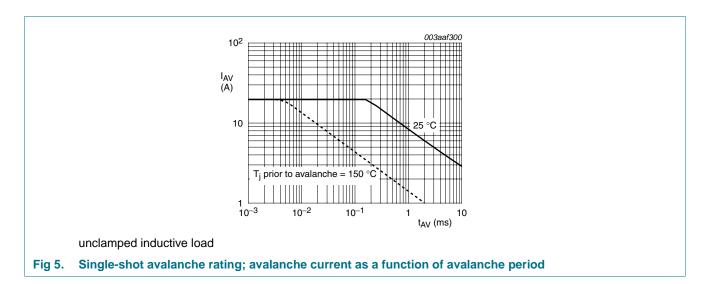


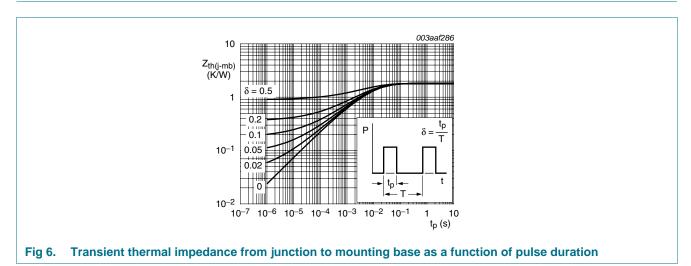
Fig 4. Normalised drain-source non-repetitive avalanche energy as a function of mounting-base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ mV}; T_j = 25 \text{ °C}$	55	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ mV}; T_j = -55 ^{\circ}\text{C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.3	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
DOON	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	26.5	38	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	24	32	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C}$	-	-	70	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	26	35	mΩ
Dynamic (characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	880	1173	pF
C _{oss}	output capacitance	T _j = 25 °C	-	165	198	pF
C_{rss}	reverse transfer capacitance		-	111	152	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	6	9	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	36	55	ns
t _{d(off)}	turn-off delay time		-	96	134	ns
t _f	fall time		-	73	102	ns
L _D	internal drain inductance	measured from contact screw on tab to centre of die ; $T_j = 25$ °C	-	3.5	-	nΗ
		from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25~^{\circ}\text{C}$	-	7.5	-	nΗ
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.85	1.2	V
		$I_S = 34 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	1.1	-	V
t _{rr}	reverse recovery time	$I_S = 34 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = -10 \text{ V};$	-	36	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	0.07	-	μC

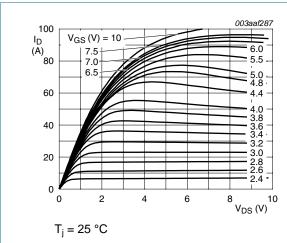


Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values

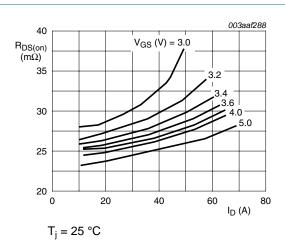


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

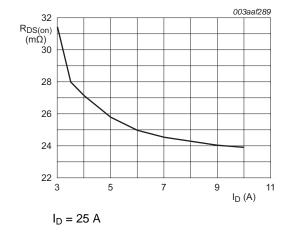


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

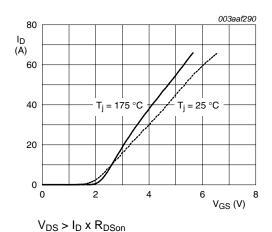
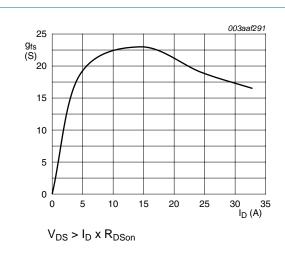
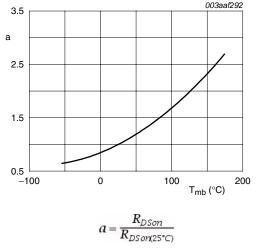


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



drain current; typical values



 $I_D = 25 \text{ A}; V_{GS} = 5 \text{ V}$

Fig 11. Forward transconductance as a function of Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

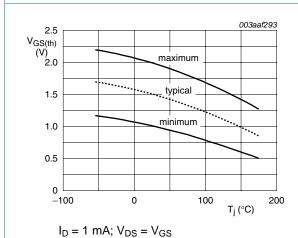
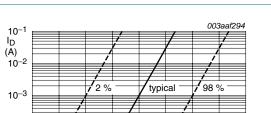


Fig 13. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25$ °C; $V_{DS} = V_{GS}$

1.0

10-4

10⁻⁵

10-6

0.5



1.5

V_{GS} (V)

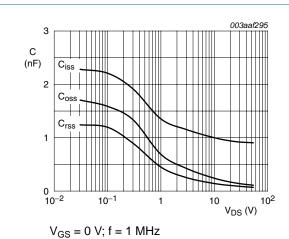
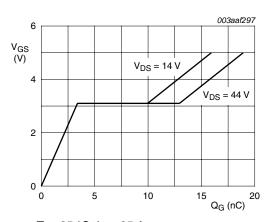
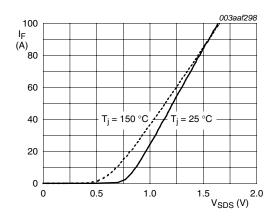


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25 \, ^{\circ}C; I_D = 25 \, A$

Fig 16. Gate-source voltage as a function of gate charge; typical values



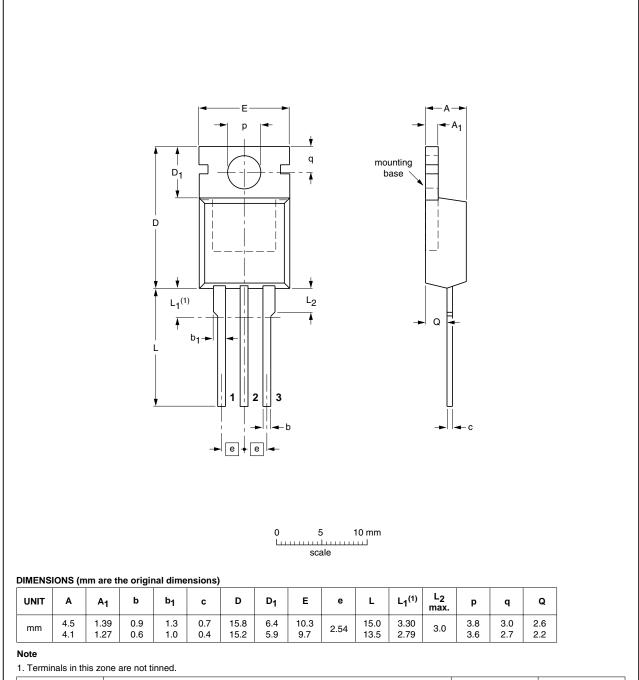
 $V_{GS} = 0 V$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78A		3-lead TO-220AB	SC-46		03-01-22 05-03-14

Fig 18. Package outline SOT78A (TO-220AB)

BUK9535-55

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9535-55A v.2	20110428	Product data sheet	-	BUK9535_9635-55A v.1
Modifications:		f this data sheet has been NXP Semiconductors.	n redesigned to com	ply with the new identity
	 Legal texts h 	ave been adapted to the	new company name	where appropriate.
	 Type numbe 	r BUK9535-55A separate	d from data sheet Bl	JK9535_9635-55A v.1.
BUK9535_9635-55A v.1	20000201	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BUK9535-55A

N-channel TrenchMOS logic level FET

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